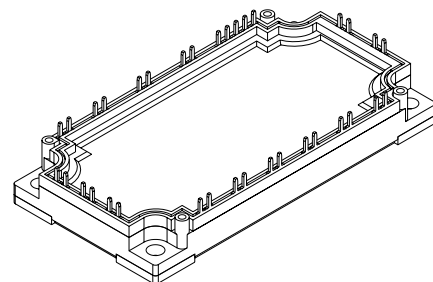
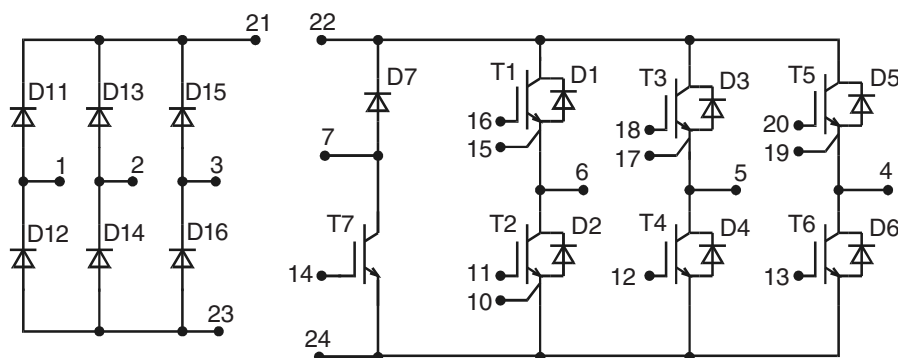
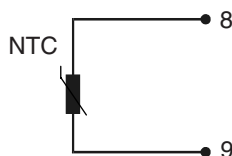


Converter - Brake - Inverter Module (CBI3)



Preliminary data



Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{FAVM} = 70 \text{ A}$	$I_{C25} = 52 \text{ A}$	$I_{C25} = 90 \text{ A}$
$I_{FSM} = 700 \text{ A}$	$V_{CE(sat)} = 2.2 \text{ V}$	$V_{CE(sat)} = 1.9 \text{ V}$

Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings	
V_{RRM}		1600	V
I_{FAV}	$T_C = 80^\circ\text{C}$; sine 180°	50	A
I_{DAVM}	$T_C = 80^\circ\text{C}$; rectangular; $d = 1/3$; bridge	140	A
I_{FSM}	$T_{VJ} = 25^\circ\text{C}$; $t = 10 \text{ ms}$; sine 50 Hz	700	A
P_{tot}	$T_C = 25^\circ\text{C}$	135	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 50 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.1 1.1	1.3 V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.8	0.05 mA mA
R_{thJC}	(per diode)			0.94 K/W

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- electric braking operation

Features

- High level of integration - only one power semiconductor module required for the whole drive
- IGBT technology with low saturation voltage, low switching losses and tail current, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with Hyperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	1200	V
V_{GES}	Continuous	± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	90	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	62	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15\text{ V}$; $R_G = 22\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ RBSOA; Clamped inductive load; $L = 100\ \mu\text{H}$	100 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = 900\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 22\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	350	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 50\text{ A}$; $V_{GE} = 15\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 2.1		2.4 V
$V_{GE(th)}$	$I_C = 2\text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.8		0.8 mA
I_{GES}	$V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}$; $I_C = 50\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_G = 22\ \Omega$	80		ns
		50		ns
		680		ns
		30		ns
		6		mJ
		4		mJ
C_{les}	$V_{CE} = 25\text{ V}$; $V_{GE} = 0\text{ V}$; $f = 1\text{ MHz}$	3.8		nF
Q_{Gon}	$V_{CE} = 600\text{ V}$; $V_{GE} = 15\text{ V}$; $I_C = 50\text{ A}$	350		nC
R_{thJC}	(per IGBT)			0.35 K/W

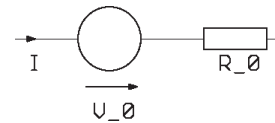
Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^{\circ}\text{C}$	110	A
I_{F80}	$T_C = 80^{\circ}\text{C}$	70	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 50\text{ A}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1 1.5		2.5 V
I_{RM} t_{rr}	$I_F = 60\text{ A}$; $di_F/dt = -500\text{ A}/\mu\text{s}$; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 600\text{ V}$; $V_{GE} = 0\text{ V}$	41		A
		200		ns
R_{thJC}	(per diode)			0.61 K/W

Equivalent Circuits for Simulation

Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}$; $T_J = 125^{\circ}\text{C}$)
T1-T6

$$V_0 = 0.98\text{ V}; R_0 = 23.2\text{ m}\Omega$$

T7

$$V_0 = 0.95\text{ V}; R_0 = 45\text{ m}\Omega$$

Diode (typ. at $T_J = 125^{\circ}\text{C}$)

D1-D6

$$V_0 = 1.27\text{ V}; R_0 = 5.8\text{ m}\Omega$$

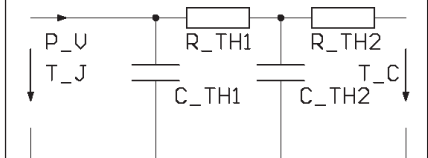
D7

$$V_0 = 1.25\text{ V}; R_0 = 31.2\text{ m}\Omega$$

D11-D16

$$V_0 = 0.83\text{ V}; R_0 = 5.5\text{ m}\Omega$$

Thermal Response



IGBT (typ.)

T1-T6

$$C_{th1} = 0.206\text{ J/K}; R_{th1} = 0.262\text{ K/W}$$

$$C_{th2} = 1.307\text{ J/K}; R_{th2} = 0.088\text{ K/W}$$

T7

$$C_{th1} = 0.128\text{ J/K}; R_{th1} = 0.421\text{ K/W}$$

$$C_{th2} = 0.961\text{ J/K}; R_{th2} = 0.129\text{ K/W}$$

Diode (typ.)

D1-D6

$$C_{th1} = 0.138\text{ J/K}; R_{th1} = 0.48\text{ K/W}$$

$$C_{th2} = 0.957\text{ J/K}; R_{th2} = 0.13\text{ K/W}$$

D7

$$C_{th1} = 0.038\text{ J/K}; R_{th1} = 1.74\text{ K/W}$$

$$C_{th2} = 0.435\text{ J/K}; R_{th2} = 0.36\text{ K/W}$$

D11-D16

$$C_{th1} = 0.086\text{ J/K}; R_{th1} = 0.738\text{ K/W}$$

$$C_{th2} = 0.621\text{ J/K}; R_{th2} = 0.202\text{ K/W}$$

Brake Chopper T7

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	1200	V
V_{GES}	Continuous	± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	52	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	35	A
I_{CM}	$V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$	50	A
V_{CEK}	RBSOA; Clamped inductive load; $L = 100\ \mu\text{H}$	V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = 900\text{ V}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	225	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 35\text{ A}$; $V_{GE} = 15\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.2 2.5	V V
$V_{GE(th)}$	$I_C = 1\text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	mA mA
I_{GES}	$V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_t E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}$; $I_C = 35\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$		85 50 440 50 2.6	ns ns ns ns mJ
C_{ies}			2	nF
Q_{Gon}			150	nC
R_{thJC}				0.55 K/W

Brake Chopper D7

Symbol	Conditions	Maximum Ratings	
V_{RRM}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	1200	V
I_{F25}	$T_C = 25^{\circ}\text{C}$	25	A
I_{F80}	$T_C = 80^{\circ}\text{C}$	16	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 35\text{ A}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		3.0 2.3	V V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	mA mA
I_{RM} t_{rr}	$I_F = 15\text{ A}$; $di_F/dt = -400\text{ A}/\mu\text{s}$; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 600\text{ V}$		16 130	A ns
R_{thJC}				2.1 K/W

Temperature Sensor NTC

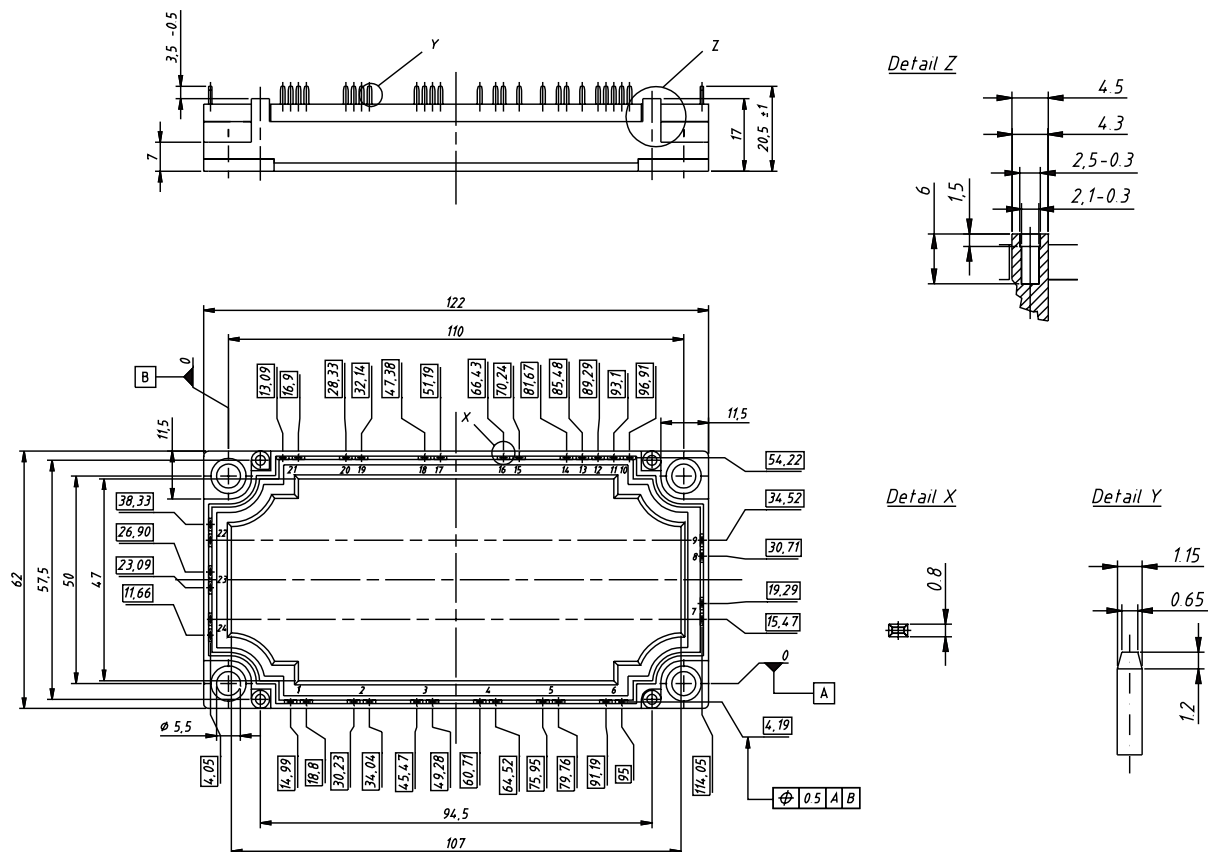
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R ₂₅	T = 25°C	4.75	5.0	5.25 kΩ
B _{25/50}			3375	K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	°C
T_{JM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	3 - 6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{pin-chip}			5	mΩ
d_S	Creepage distance on surface	6		mm
d_A	Strike distance in air	6		mm
R_{thCH}	with heatsink compound		0.01	K/W
Weight			300	g

Dimensions in mm (1 mm = 0.0394")



Input Rectifier Bridge D11 - D16

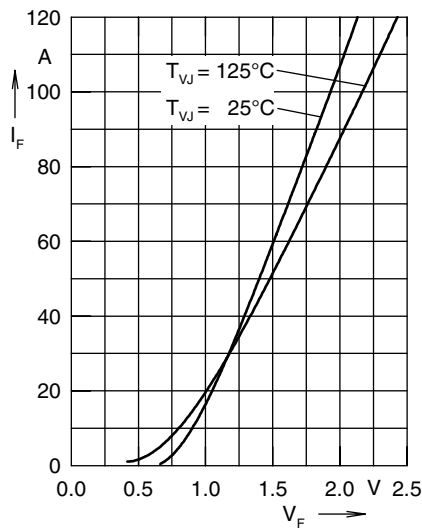


Fig. 1 Forward current versus voltage drop per diode

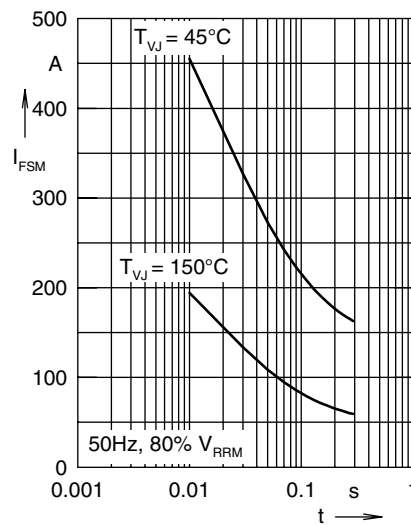


Fig. 2 Surge overload current

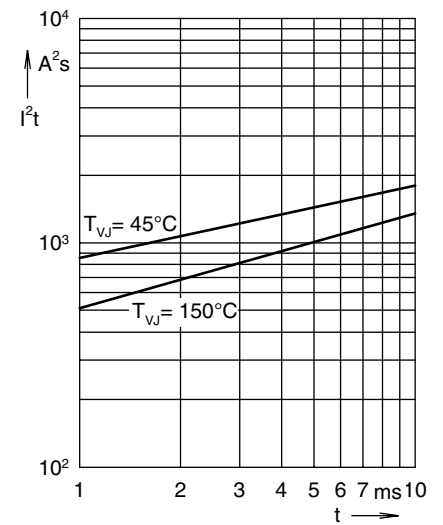


Fig. 3 I^2t versus time per diode

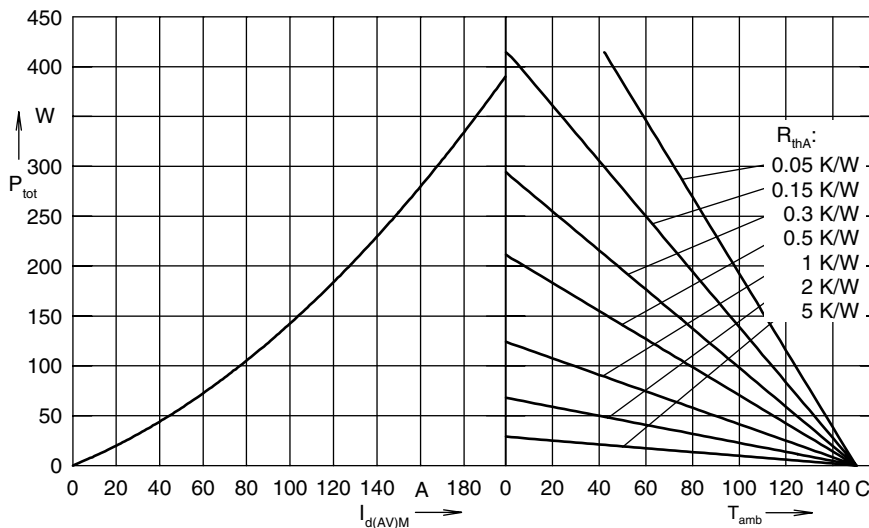


Fig. 4 Power dissipation versus direct output current and ambient temperature, sin 180°

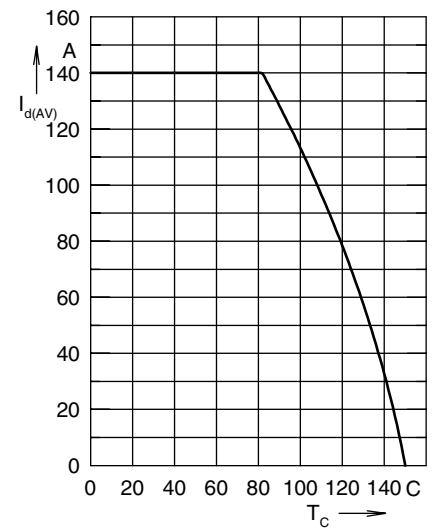


Fig. 5 Max. forward current versus case temperature

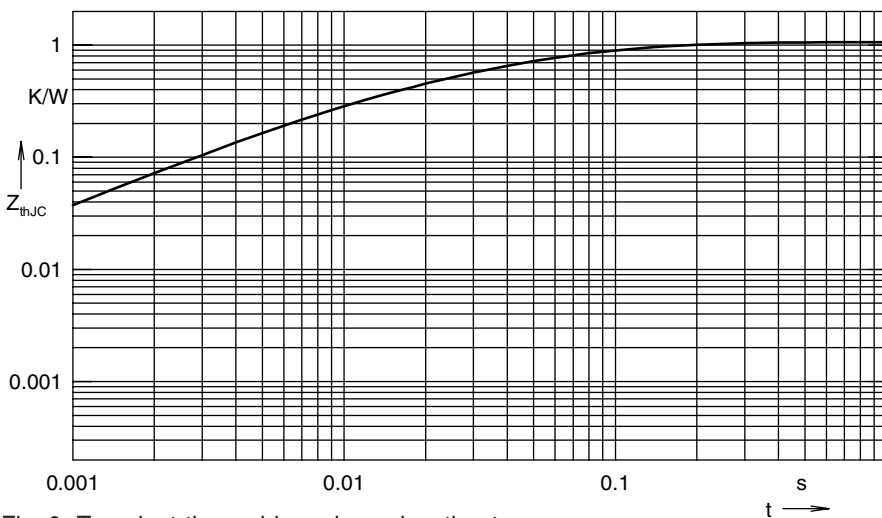


Fig. 6 Transient thermal impedance junction to case

Output Inverter T1 - T6 / D1 - D6

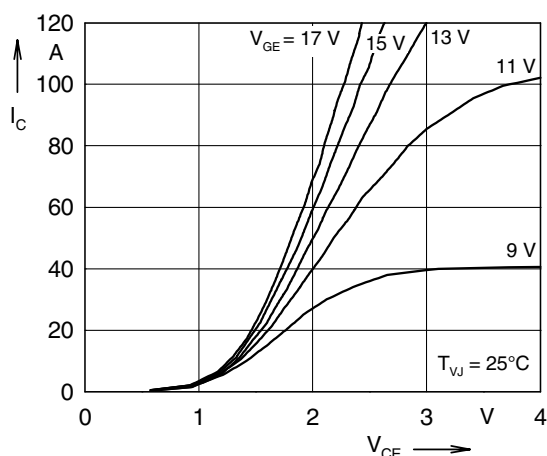


Fig. 7 Typ. output characteristics

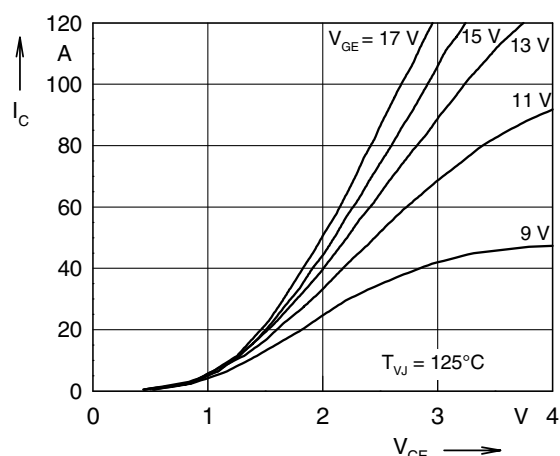


Fig. 8 Typ. output characteristics

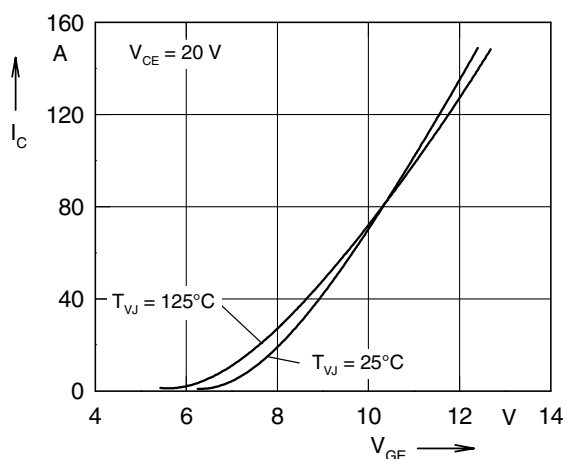


Fig. 9 Typ. transfer characteristics

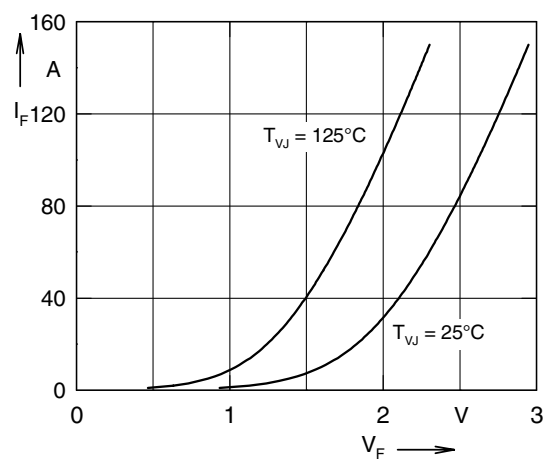


Fig. 10 Typ. forward characteristics of free wheeling diode

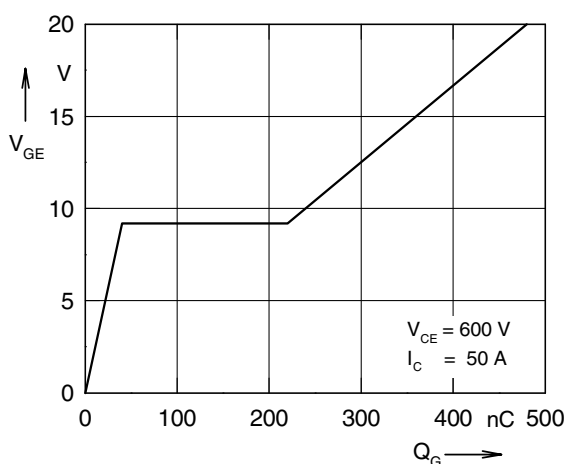


Fig. 11 Typ. turn on gate charge

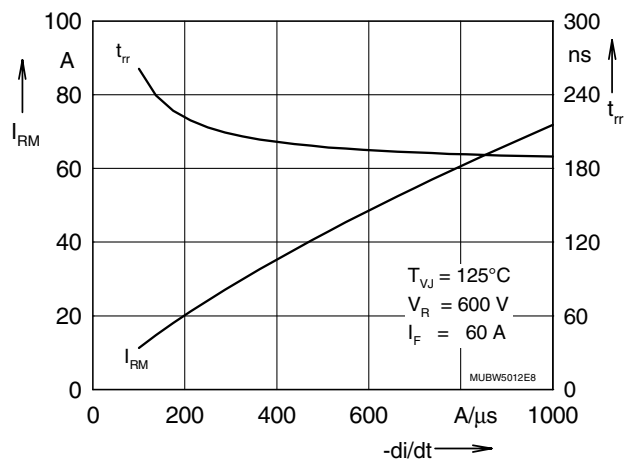


Fig. 12 Typ. turn off characteristics of free wheeling diode

Output Inverter T1 - T6 / D1 - D6

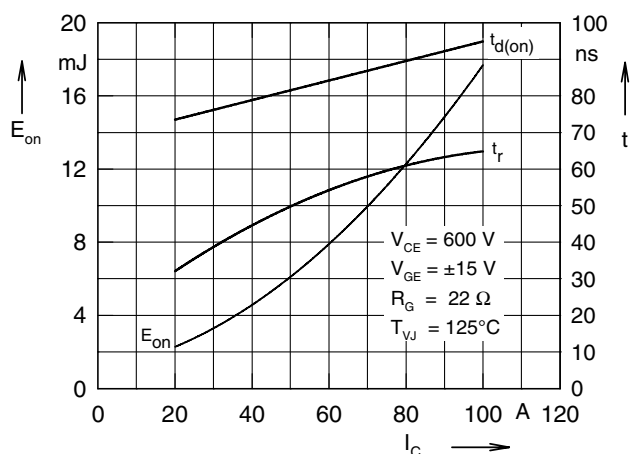


Fig. 13 Typ. turn on energy and switching times versus collector current

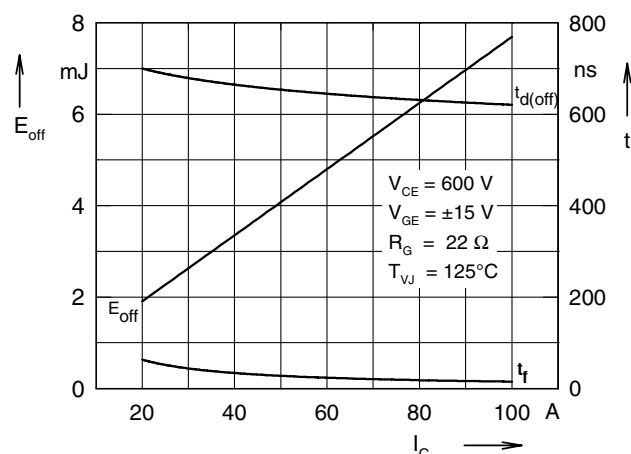


Fig. 14 Typ. turn off energy and switching times versus collector current

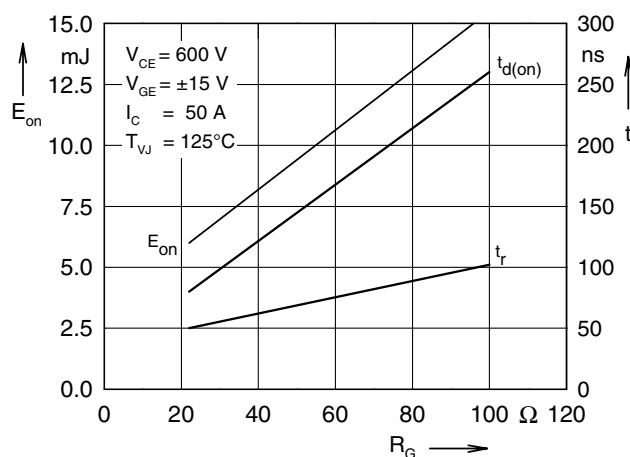


Fig. 15 Typ. turn on energy and switching times versus gate resistor

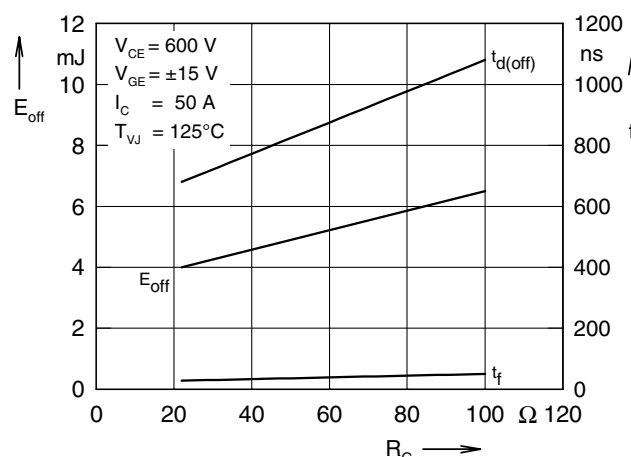


Fig. 16 Typ. turn off energy and switching times versus gate resistor

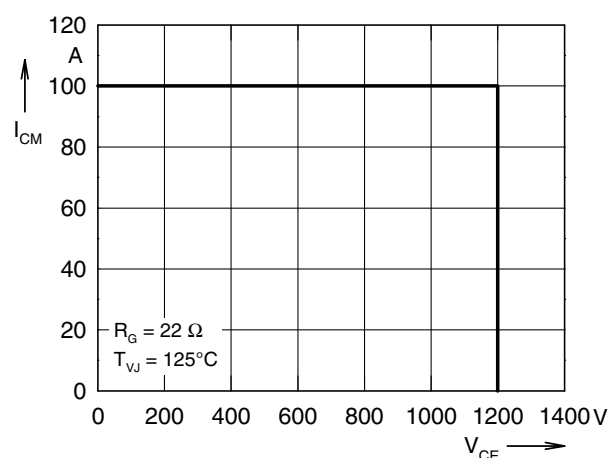


Fig. 17 Typ. turn off characteristics of free wheeling diode

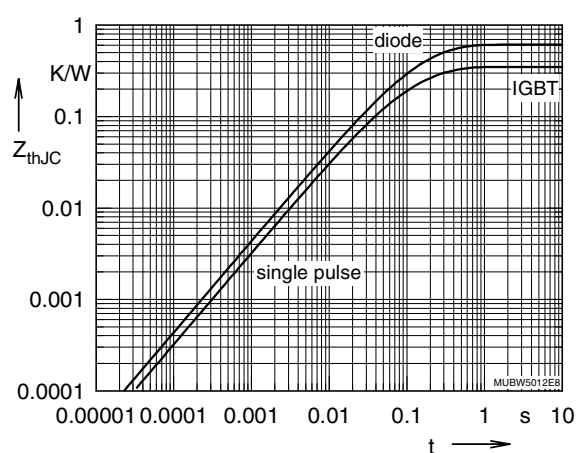


Fig. 18 Typ. turn off characteristics of free wheeling diode

Brake Chopper T7 / D7

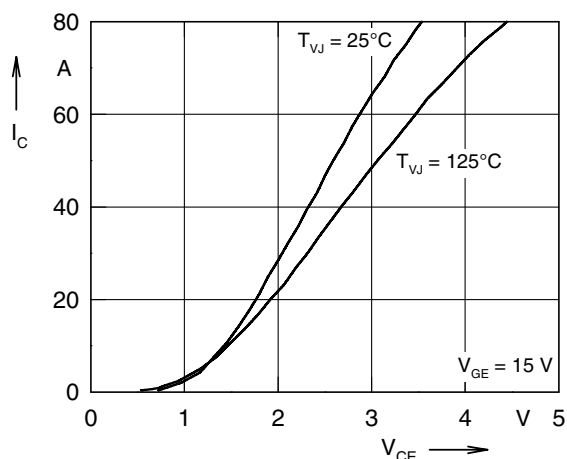


Fig. 19 Typ. output characteristics

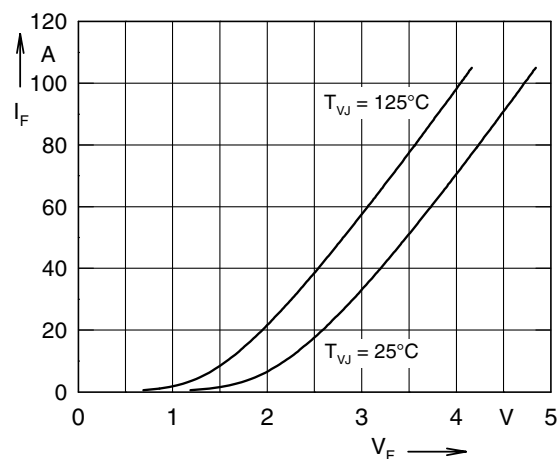


Fig. 20 Typ. forward characteristics of free wheeling diode

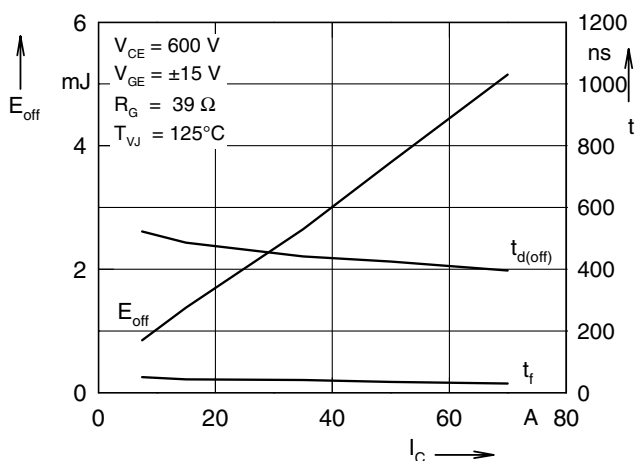


Fig. 21 Typ. turn off energy and switching times versus collector current

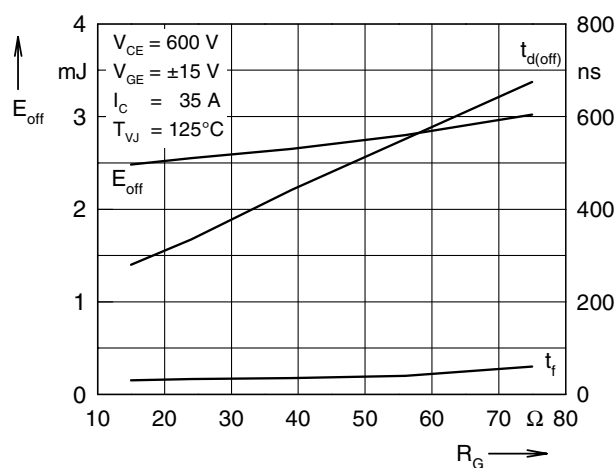


Fig. 22 Typ. turn off energy and switching times versus gate resistor

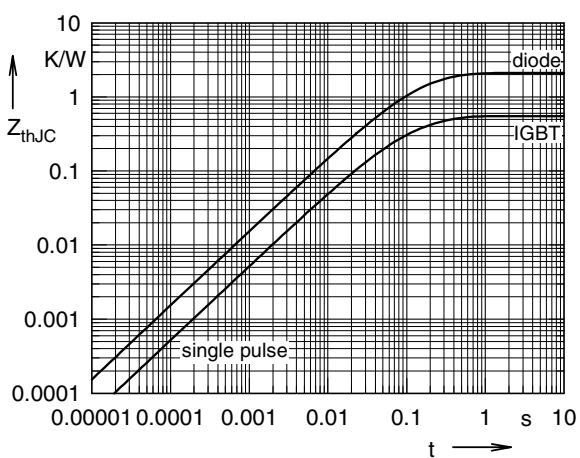


Fig. 23 Typ. transient thermal impedance

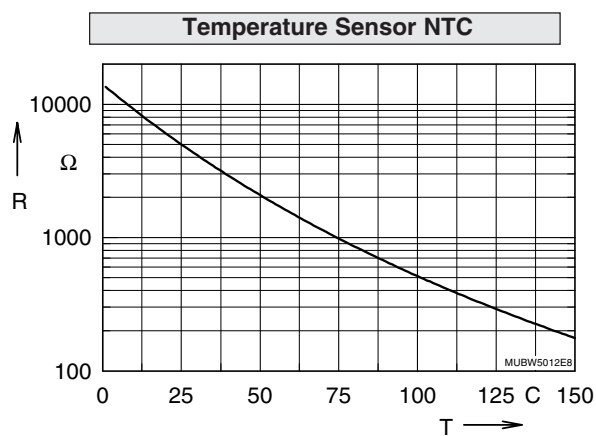


Fig. 24 Typ. thermistorresistance versus temperature